

	Type	L #	Hits	Search Text	DBS	Time Stamp	Comments	Error Definition
1	BRS	L1	655360	memory or storage	USPAT	2000/11/17 16:19		
2	BRS.	L2	26065	eprom or eeprom	USPAT	2000/11/17 16:19		
3	BRS	L3	656303	11 or 12	USPAT	2000/11/17 16:21		
4	BRS	L4	13082	multilevel or (multi-level)	USPAT	2000/11/17 16:22		
5	BRS	L5	1521	multivalue or (multi-value)	USPAT	2000/11/17 16:23		
6	BRS	L6	1102	multistate or (multi-state)	USPAT	2000/11/17 16:24		
7	BRS	L7	8658	multibit or (multi-bit)	USPAT	2000/11/17 16:24		
8	BRS	L8	23226	14 or 15 or 16 or 17	USPAT	2000/11/17 16:25		
9	BRS	L9	2200	18 adj5 13	USPAT	2000/11/17 16:27		
10	BRS	L10	140109	write or writing	USPAT	2000/11/17 16:28		
11	BRS	L11	253347	program or programming	USPAT	2000/11/17 16:30		
12	BRS	L12	331474	110 or 111	USPAT	2000/11/17 16:31		
13	BRS	L13	64833	verify or verifying or verification	USPAT	2000/11/17 16:33		
14	BRS	L14	3748	112 near3 113	USPAT	2000/11/17 16:36		
15	BRS	L15	205	19 and 114	USPAT	2000/11/17 16:37		

	U	1	Document ID	Issue Date	Pages	Title	Current OR
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6147911 A	20001114	77	Nonvolatile semiconductor memory device	365/185.28
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6141253 A	20001031		Electrically programmable semiconductor device with concurrent program and verification operations	365/185.28
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6137729 A	20001024		Method for erasing memory cells in a flash memory device	365/185.29
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6134148 A	20001017		Semiconductor integrated circuit and data processing system	365/185.28
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6134145 A	20001017		High data rate write process for non-volatile flash memories	365/185.22
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6134141 A	20001017		Dynamic write process for high bandwidth multi-bit-per-cell and analog/multi-level non-volatile memories	365/185.03
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6134140 A	20001017		Nonvolatile semiconductor memory device with soft-programming to adjust erased state of memory cells	365/185.03
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6133098 A	20001017		Process for making and programming and operating a dual-bit multi-level ballistic flash memory	438/267

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
1	365/185.23		Takeuchi, Ken , et al.	<input type="checkbox"/>						
2	365/185.03 ; 365/185.2		Lin, Chin-His	<input type="checkbox"/>						
3	365/185.11		Choi, Ki-Hwan	<input type="checkbox"/>						
4	365/185.03		Kawahara, Takayuki , et al.	<input type="checkbox"/>						
5	365/185.11 ; 365/185.28		Wong, Sau C.	<input type="checkbox"/>						
6	365/185.22 ; 365/185.25		Wong, Sau-Ching	<input type="checkbox"/>						
7	365/185.17 ; 365/185.22		Tanaka, Tomoharu , et al.	<input type="checkbox"/>						
8			Ogura, Seiki , et al.	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6128229 A	200001003		Non-volatile semiconductor memory and method of verifying after writing and reading the same	365/185.22
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6128224 A	200001003		Method and apparatus for writing an erasable non-volatile memory	365/185.18
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6122193 A	200000919		Non-volatile semiconductor memory capable of storing 1-bit data or multi-bit data	365/185.03
12	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6118696 A	200000912		Multi-bit memory cell array of a non-volatile semiconductor memory	365/185.11
13	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6118692 A	200000912		device and method for driving the same	
14	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6115290 A	200000905		Memory apparatus including programmable non-volatile multi-bit memory	365/185.03
15	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6115285 A	200000905		cell, and apparatus and method for demarcating memory states of the cell	365/185.25
16	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6111790 A	200000829		Mechanism for resetting sense circuitry to a known state in a nonvolatile memory device	365/185.24

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
9	365/185.03 ; 365/185.17 ; 365/185.25		Nobukata, Hiromi	<input type="checkbox"/>						
10	365/185.22		Morton, Bruce Lee , et al.	<input type="checkbox"/>						
11	365/185.09 ; 365/185.12 ; 365/185.17 ; 365/185.18 ; 365/185.22		Shibata, Noboru , et al.	<input type="checkbox"/>						
12	365/185.13 ; 365/185.17		Choi, Jung-Dal	<input type="checkbox"/>						
13	365/168		Banks, Gerald J.	<input type="checkbox"/>						
14	365/185.21 ; 365/233.5						<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
15	365/185.2 ; 365/185.26		Montanari, Donato , et al.	<input type="checkbox"/>						
16	365/185.18		Miwa, Hitoshi , et al.	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
17	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6112314 A	200000829		Apparatus and method for detecting over-programming condition in multistate memory device	714/37
18	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6108326 A	200000822		Microchips and remote control devices comprising same	370/342
19	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6102963 A	200000815		Electrically erasable and reprogrammable, nonvolatile integrated storage device with in-system programming and verification (ISPAV) capabilities	716/17
20	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6104640 A	200000815		for supporting in-system reconfiguring of PLD's Electrically alterable non-violatile memory with N-bits per cell	365/189.01
21	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6097628 A	200000801		Multi-level memory circuit with regulated writing voltage	365/185.03
22	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6097637 A	200000801		Dynamic single bit per cell to multiple bit per cell memory	365/185.03
23	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6097635 A	200000801		Sensing circuit for programming/reading multilevel flash memory	365/185.21
24	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6097634 A	200000801		Latch-type sensing circuit and program-verify circuit	365/185.21

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
17			Norman, Robert D., et al.	<input type="checkbox"/>						
18	340/825.31		Bruwer, Frederick	<input type="checkbox"/>						
19	365/185.33		Agrawal, Om P.	<input type="checkbox"/>						
20	365/168 ; 365/230.01		Banks, Gerald J.	<input type="checkbox"/>						
21	365/185.18 ; 365/185.23		Roldani, Paolo	<input type="checkbox"/>						
22	365/168		Bauer, Mark E., et al.	<input type="checkbox"/>						
23	365/185.03 ; 365/185.2		Chang, Seung-Ho	<input type="checkbox"/>						
24	365/185.03 ; 365/205		Sugiyama, Toshinobu	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
25	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6097059 A	200000801			Transistor, transistor array, method for manufacturing transistor array, and nonvolatile semiconductor memory	257/321
26	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6094368 A	200000725			Auto-tracking write and read processes for multi-bit-per-cell non-volatile memories	365/49
27	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6091618 A	200000718			Method and circuitry for storing discrete amounts of charge in a single memory element	365/45
28	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6091631 A	200000718			Program/verify technique for multi-level flash cells enabling different threshold levels to be simultaneously programmed	365/185.03
29	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6091642 A	200000718			Method for controlled erasing memory devices, in particular analog and multi-level flash-EEPROM devices	365/185.29
30	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6091640 A	200000718			Semiconductor integrated circuit with multiple write operation modes	365/185.28
31	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6078518 A	200000620			Apparatus and method for reading state of multistate non-volatile memory cells	365/185.03

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
25	257/315 ; 257/316 ; 257/319		Yamada, Kouichi	<input type="checkbox"/>						
26	365/185.03 ; 365/185.11		Ching, Wong Sau	<input type="checkbox"/>						
27	365/168		Fazio, Albert , et al.	<input type="checkbox"/>						
28	365/185.33		Kucera, Joe , et al.	<input type="checkbox"/>						
29	365/185.24 ; 365/185.3			<input type="checkbox"/>						
30	365/185.22		Kawahara, Takayuki , et al.	<input type="checkbox"/>						
31	365/168 ; 365/185.2 ; 365/207 ; 365/208		Chevallier, Christophe J.	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
32	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6075727 A	200000613		Method and apparatus for writing an erasable non-volatile memory	365/185.22
33	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6075738 A	200000613		Semiconductor memory device	365/210
34	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6069823 A	200000530		Nonvolatile semiconductor memory device	365/185.22
						Nonvolatile semiconductor memory with single-bit and multi-bit modes of operation and method for performing programming and reading operations	365/185.03
35	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6067248 A	200000523		Memory system	365/185.03
36	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6064591 A	200000516		Semiconductor memory device	365/203
37	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6064611 A	200000516		Semiconductor nonvolatile memory device and method of data programming	365/185.03
38	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6058042 A	200000502		the same	365/218
39	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6058060 A	200000502		Multi-bit-per-cell and analog/multi-level non-volatile memories with improved resolution and signal-to noise ratio	365/185.03
40	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6055181 A	200000425		Nonvolatile semiconductor memory device capable of storing multi-value data of more than one bit in a memory cell	365/185.03

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
32	365/185.29 ; 365/218		Morton, Bruce Lee , et al.	<input type="checkbox"/>						
33	365/189.01		Takano, Yoh	<input type="checkbox"/>						
34	365/185.03		Takeuchi, Ken , et al.	<input type="checkbox"/>						
35	365/185.09		YOO, Tae-Hwa	<input type="checkbox"/>						
36	365/168		Takeuchi, Ken , et al.	<input type="checkbox"/>						
37			Tanaka, Tomoharu , et al.	<input type="checkbox"/>						
38	365/185.12 ; 365/185.18 ; 365/185.22 ; 365/185.25		Nobukata, Hiromi	<input type="checkbox"/>						
39	365/185.03 ; 365/185.24 ; 365/185.33		Wong, Sau C.	<input type="checkbox"/>						
40	365/185.17 ; 365/185.22		Tanaka, Tomoharu , et al.	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
41	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6055188 A	20000425			Nonvolatile semiconductor memory device having a data circuit for erasing and writing operations	365/185.22
42	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6049494 A	20000411			Semiconductor memory device	365/203
43	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6049899 A	20000411			Soft errors handling in EEPROM devices	714/721
44	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6046934 A	20000404			Method and device for multi-level programming of a memory cell	365/185.03
45	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6046933 A	20000404			Nonvolatile semiconductor memory device and IC memory card using same	365/185.03
46	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6046936 A	20000404			Semiconductor, memory card, and data processing system	365/185.03
47	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6046935 A	20000404			Semiconductor device and memory system	365/185.03
48	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6044013 A	20000328			Nonvolatile semiconductor memory device	365/185.03
49	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6044019 A	20000328			Non-volatile memory with improved sensing and method therefor	365/185.21
50	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6040605 A	20000321			Semiconductor memory device	257/369
51	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6040993 A	20000321			Method for programming an analog/multi-level flash EEPROM	365/185.03

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
41	365/185.03 ; 365/185.17	Takeuchi, Ken , et al.								
42	365/185.25	Sakui, Koji , et al.								
43	365/184 ; 365/185.03 ; 365/201 ; 714/764 ; 714/766	Auclair, Daniel L. , et al.								
44	365/185.19 ; 365/185.2 ; 365/185.21	Lin, Chin Hsi								
45	365/185.23 ; 365/52	Nobukata, Hiromi , et al.								
46	365/185.17 ; 365/185.22 365/185.18	Tsujiikawa, Tetsuya , et al.								
47	365/189.05 ; 365/221	Takeuchi, Ken , et al.								
48	365/185.22	Tanaka, Tomoharu , et al.								
49	365/185.2 ; 365/189.07 ; 365/189.09 ; 365/207	Cerneia, Raul-Adrian , et al.								
50	257/314 ; 257/368 ; 257/390 ; 257/66	Sano, Toshiaki , et al.								
51	365/185.19 ; 365/185.22	Chen, Chia-Hsing , et al.								

	U	1	Document ID	Issue Date	Pages	Title	Current OR
52	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6038167 A	20000314		Nonvolatile memory device and refreshing method	365/185.03
53	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6038166 A	20000314		High resolution multi-bit-per-cell memory	365/185.03
54	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6038165 A	20000314		Nonvolatile memory device and refreshing method	365/185.03
55	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6038174 A	20000314		Precision programming of nonvolatile memory cells	365/185.28
56	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6038169 A	20000314		Read reference scheme for flash memory	365/185.11
57	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6034892 A	20000307		Nonvolatile memory cell and method for programming and/or verifying the same	365/185.14
58	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6031774 A	20000229		Internal power supply voltage generating circuit and the method for controlling thereof	365/204
59	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6028793 A	20000222		High voltage driver circuit for a decoding circuit in multilevel non-volatile memory devices	365/185.23
60	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6028792 A	20000222		Multi-level memory for verifying programming results	365/185.22
61	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6026015 A	20000215		Non-volatile multi-level semiconductor storage device for storing multiple bits using multiple variable threshold voltages	365/185.03
62	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6026014 A	20000215		Nonvolatile semiconductor memory and read method	365/185.03

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
52	365/185.22		Miwa, Hitoshi , et al.	□	□	□	□	□	□	□
53	365/185.21 ; 365/236		Wong, Sau C.	□	□	□	□	□	□	□
54	365/185.22		Miwa, Hitoshi , et al.	□	□	□	□	□	□	□
55	365/185.03 ; 365/185.18		Khan, Sakhawat M. , et al.	□	□	□	□	□	□	□
56	365/185.2 ; 365/185.33		Ogura, Seiki , et al.	□	□	□	□	□	□	□
57	365/185.01 ; 365/185.28		Choi, Woong Lim	□	□	□	□	□	□	□
58	365/185.25 ; 365/185.33		Chung, Hwi-Taek	□	□	□	□	□	□	□
59	365/189.11 ; 365/230.06		Manstretta, Alessandro , et al.	□	□	□	□	□	□	□
60	365/185.03 ; 365/185.24		Tanaka, Tomoharu , et al.	□	□	□	□	□	□	□
61	365/185.24		Hirakawa, Tsuyoshi	□	□	□	□	□	□	□
62	365/185.24		Sato, Hiroshi , et al.	□	□	□	□	□	□	□

	U	1	Document ID	Issue Date	Pages	Title	Current OR
63	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6014327 A	200000111			Memory apparatus including programmable non-volatile multi-bit memory	365/185.03
64	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6014330 A	200000111			Memory apparatus and apparatus and method for demarcating memory <small>States of the cell</small>	365/185.17
65	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6011716 A	200000104			Memory apparatus including programmable non-volatile multi-bit memory	365/185.03
66	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6011715 A	200000104			Memory apparatus and apparatus and method for demarcating memory <small>States of the cell</small>	365/185.03
67	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6009015 A	19991228			Method for multilevel programming of a nonvolatile memory, and a multilevel nonvolatile memory	365/185.22
68	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6005805 A	19991221			Program-verify circuit and program-verify method	365/185.22
69	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6002152 A	19991214			Nonvolatile semiconductor device with a verify function	365/185.22
70	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 6002614 A	19991214			EEPROM with split gate source side injection with sidewall spacers	257/316
						Memory apparatus including programmable non-volatile multi-bit memory	365/189.01
						Memory apparatus and apparatus and method for demarcating memory <small>States of the cell</small>	365/189.01

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
63	365/168	Banks, Gerald J.	<input type="checkbox"/>							
64	365/185.18 ; 365/185.19	Endoh, Tetsuo , et al.	<input type="checkbox"/>							
65	365/168	Banks, Gerald J.	<input type="checkbox"/>							
66	365/185.19 ; 365/185.24	Pasotti, Marco , et al.	<input type="checkbox"/>							
67	365/185.01 ; 365/185.24 ; 365/230.08	Sugiyama, Toshinobu	<input type="checkbox"/>							
68	365/185.2 ; 365/210	Takeuchi, Nobuyoshi	<input type="checkbox"/>							
69	257/326	Guterman, Daniel C. , et al.	<input type="checkbox"/>							
70	365/189.09	Banks, Gerald J.	<input type="checkbox"/>							

	U	1	Document ID	Issue Date	Pages	Title	Current OR
71	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5999451 A	19991207		Byte-wide write scheme for a page flash device	365/185.11
72	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5995412 A	19991130		Nonvolatile semiconductor storage device and writing method thereof	365/185.03
73	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5991517 A	19991123		Flash EEPROM system with cell by cell programming verification	714/3
74	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5986929 A	19991116		Multi-level nonvolatile semiconductor memory device	365/185.03
75	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5986939 A	19991116		Non-volatile semiconductor memory device	365/185.29
						Nonvolatile semiconductor memory device for storing multivalue	
76	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5982667 A	19991109		information by controlling erase and plural write states of each memory cell	365/185.22
77	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5982663 A	19991109		Nonvolatile semiconductor memory performing single bit and multi-bit operations	365/185.09
78	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5982662 A	19991109		Semiconductor memory device with improved read characteristics for data having multi values	365/185.03
79	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5983329 A	19991109		Caching virtual memory locks	711/163

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
71	365/185.12 ; 365/189.02	Lin, Jin-Lien , et al.		<input type="checkbox"/>						
72	365/185.22	Ohta, Yoshiiji		<input type="checkbox"/>						
73	714/8	Harari, Eliyahou , et al.		<input type="checkbox"/>						
74	365/185.21 ; 365/185.22	Sugiura, Yoshihisa , et al.		<input type="checkbox"/>						
75	365/185.14 ; 365/185.18 ; 365/185.2 ; 365/185.21	Yamada, Kouichi		<input type="checkbox"/>						
76	365/185.03 ; 365/185.19 ; 365/185.29	Jyouno, Yusuke , et al.		<input type="checkbox"/>						
77	365/185.03 ; 365/185.22	Park, Jong-Wook		<input type="checkbox"/>						
78	365/185.2 ; 365/185.21	Kobayashi, Yasuhiro , et al.		<input type="checkbox"/>						
79	711/145 ; 711/150 ; 711/152	Thaler, Wolfgang J. , et al.		<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
80	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5969986 A	19991019		High-bandwidth read and write architectures for non-volatile memories	365/185.03
81	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5969985 A	19991019		Nonvolatile semiconductor memory device	365/185.03
82	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5966332 A	19991012		Floating gate memory cell array allowing cell-by-cell erasure	365/185.29
83	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5949716 A	19990907		Look-ahead erase for sequential data storage	365/185.29
84	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5946231 A	19990831		Non-volatile semiconductor memory device	365/185.03
85	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5940704 A	19990817		Method of manufacturing a reference apparatus	438/257
86	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5933366 A	19990803		Multistate memory device with reference bit lines	365/185.03
87	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5930172 A	19990727		Page buffer for a multi-level flash memory with a limited number of latches per memory cell	365/185.21
88	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5930167 A	19990727		Multi-state non-volatile flash memory capable of being its own two state write cache	365/185.03
89	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5923590 A	19990713		Device for reading cells of a memory	365/189.01
90	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5923587 A	19990713		Multi-bit memory cell array of a non-volatile semiconductor memory device and method for driving the same	365/185.11

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
80	365/185.11 ; 365/185.19 ; 365/185.21 ; 365/185.33		Wong, Sau C. , et al.	□	□	□	□	□	□	□
81	365/230.06		Tanaka, Tomoharu , et al.	□	□	□	□	□	□	□
82	365/185.28		Takano, Yoh	□	□	□	□	□	□	□
83	365/185.24 ; 365/185.33		Wong, Sau C. , et al.	□	□	□	□	□	□	□
84	365/185.17 ; 365/185.19		Endoh, Tetsuo , et al.	□	□	□	□	□	□	□
85	438/275		Takeuchi, Nobuyoshi	□	□	□	□	□	□	□
86	365/185.2 ; 365/207 ; 365/210		Yoshikawa, Sadao	□	□	□	□	□	□	□
87	365/185.03 ; 365/189.05		Kucera, Joe	□	□	□	□	□	□	□
88	365/185.24 ; 365/185.33		Lee, Douglas J. , et al.	□	□	□	□	□	□	□
89	365/203 ; 365/210		Yero, Emilio	□	□	□	□	□	□	□
90	365/185.13 ; 365/185.17		Choi, Jung-Dal	□	□	□	□	□	□	□

	U	1	Document ID	Issue Date	Pages	Title	Current OR
91	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5923585 A	19990713		Source biasing in non-volatile memory having row-based sectors	365/185.03
92	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5920507 A	19990706		Nonvolatile semiconductor memory device	365/185.22
93	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5912838 A	19990615		Apparatus for reading state of multistate non-volatile memory cells	365/185.03
94	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5910925 A	19990608		EEPROM with split gate source side injection	365/230.01
95	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5910915 A	19990608		EEPROM with split gate source side injection	365/185.28
96	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5909449 A	19990601		Multibit-per-cell non-volatile memory with error detection and correction	714/721
97	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5909387 A	19990601		Memory architecture for recording of multiple messages	365/45
98	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5905674 A	19990518		Nonvolatile memory and method of programming the same	365/185.1
99	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5903495 A	19990511		Semiconductor device and memory system	365/185.03
100	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5901089 A	19990504		Stabilization circuits and techniques for storage and retrieval of	365/185.24
101	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5898614 A	19990427		single or multiple digital bits per memory cell Non-volatile semiconductor memory device	365/185.1

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
91	365/185.18		Wong, Sau C. , et al.	<input type="checkbox"/>						
92	365/185.03		Takeuchi, Ken , et al.	<input type="checkbox"/>						
93	365/168 ; 365/185.2 ; 365/207 ; 365/208		Chevallier, Christophe J.	<input type="checkbox"/>						
94	365/189.01		Guterman, Daniel C. , et al.	<input type="checkbox"/>						
95	365/185.01 ; 365/185.14 ; 365/185.22		Guterman, Daniel C. , et al.	<input type="checkbox"/>						
96			So, Hock C. , et al.	<input type="checkbox"/>						
97	365/185.29 ; 365/185.3 ; 379/88.28		Wong, Sau C. , et al.	<input type="checkbox"/>						
98	365/185.01		Choi, Woong-Lim	<input type="checkbox"/>						
99	365/185.22 ; 365/185.24		Takeuchi, Ken , et al.	<input type="checkbox"/>						
100	365/185.03 ; 365/185.19		Korsh, George J. , et al.	<input type="checkbox"/>						
101	365/185.05 ; 365/185.07		Takeuchi, Nobuyoshi	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
102	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5894435 A	19990413		Nonvolatile semiconductor memory device and method of reducing read disturbance	365/185.03
103	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5892710 A	19990406		Method and circuitry for storing discrete amounts of charge in a single memory element	365/185.03
104	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5889699 A	19990330		Non-volatile semiconductor memory device	365/185.18
105	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5889698 A	19990330		Nonvolatile memory device and refreshing method	365/185.03
106	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5890192 A	19990330		Concurrent write of multiple chunks of data into multiple subarrays of	711/103
107	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5883409 A	19990316		flash EEPROM with split gate source side injection	257/316
108	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5872735 A	19990216		Electrically alterable non-volatile memory with N-bits per cell	365/189.01
109	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5870335 A	19990209		Precision programming of nonvolatile memory cells	365/185.18
110	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5870218 A	19990209		Nonvolatile semiconductor memory device which stores multi-value information	365/185.03

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
102	365/185.02 ; 365/185.17		Nobukata, Hiromi	<input type="checkbox"/>						
103	365/185.22 ; 365/185.24	Fazio, Albert , et al.		<input type="checkbox"/>						
104	365/185.21 ; 365/185.22 ; 365/189.09 ; 365/207	Takano, Yoh		<input type="checkbox"/>						
105	365/184	Miwa, Hitoshi , et al.		<input type="checkbox"/>						
106	365/120 ; 365/189.05 ; 365/222	Lee, Douglas J. , et al.		<input type="checkbox"/>						
107	257/326	Guterman, Daniel C. , et al.		<input type="checkbox"/>						
108	365/218	Banks, Gerald J.		<input type="checkbox"/>						
109	365/185.03	Khan, Sakhawat M. , et al.		<input type="checkbox"/>						
110	365/185.18 ; 365/185.21 ; 365/185.22	Jyouno, Yusuke , et al.		<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
111	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5867429 A		19990202		High density non-volatile flash memory without adverse effects of electric field coupling between adjacent floating gates.	365/185.33
112	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5864504 A		19990126		Nonvolatile semiconductor memory with temperature compensation for read/verify referencing scheme	365/185.24
113	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5862074 A		19990119		Integrated circuit memory devices having reconfigurable nonvolatile multi-bit memory cells therein and methods of operating same	365/185.03
114	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5859454 A		19990112		Nonvolatile memory device	257/316
115	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5847996 A		19981208		Eeprom with split gate source side injection	365/185.28
116	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5847992 A		19981208		Multi-level non-volatile semiconductor memory device having improved multi-level data storing circuits	365/185.03
117	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5844841 A		19981201		Memory system	365/185.03
118	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5845068 A		19981201		Multilevel security port methods, apparatuses, and computer program products	713/200

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
111	365/185.21 ; 365/185.26	Chen, Jian , et al.		<input type="checkbox"/>						
112	365/185.2 ; 365/185.22 ; 365/212	Tanzawa, Toru , et al.		<input type="checkbox"/>						
113	365/185.21 ; 365/185.33	Park, Jong-Wook		<input type="checkbox"/>						
114	257/314 ; 257/321 ; 257/324	Choi, Woong Lim , et al.		<input type="checkbox"/>						
115	365/185.01 ; 365/185.26	Guterman, Daniel C. , et al.		<input type="checkbox"/>						
116	365/185.17 ; 365/185.21	Tanaka, Tomoharu , et al.		<input type="checkbox"/>						
117	365/168 ; 365/185.22	Takeuchi, Ken , et al.		<input type="checkbox"/>						
118	709/229 ; 713/201 ; 713/202	Winiger, Gary W.		<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
119	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5841698 A	19981124		Semiconductor device	365/185.21
120	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5835414 A	19981110		Page mode program, program verify, read and erase verify for floating gate memory device with low current page buffer	365/185.25
121	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5831900 A	19981103		Nonvolatile multi-level semiconductor memory device with registers	365/185.03
122	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5828601 A	19981027		Programmed reference	365/185.2
123	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5818759 A	19981006		Non-volatile semiconductor memory device	365/185.18
124	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5818757 A	19981006		Analog and multi-level memory with reduced program disturb	365/185.18
125	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5818753 A	19981006		Electrically-erasable and programmable ROM with pulse-driven memory cell	365/185.03
126	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5815439 A	19980929		Stabilization circuits and techniques for storage and retrieval of single or multiple digital bits per memory cell	365/185.24
127	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5815436 A	19980929		Multi-level nonvolatile semiconductor memory device having improved programming level and read/write multi-level data Circuits	365/185.03

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
119	327/170 ; 327/437 ; 365/185.03 ; 365/189.11	Hirano, Hiroshige , et al.		<input type="checkbox"/>						
120	365/185.12 ; 365/185.29	Hung, Chun-Hsiung , et al.		<input type="checkbox"/>						
121	365/185.23	Miyamoto, Junichi		<input type="checkbox"/>						
122	365/185.22 ; 365/210 ; 365/210	Hollmer, Shane C. , et al.		<input type="checkbox"/>						
123	365/185.2 ; 365/185.22 ; 365/210	Kobayashi, Yasuhiro		<input type="checkbox"/>						
124	365/185.23	So, Hock C. , et al.		<input type="checkbox"/>						
125	365/185.13 ; 365/185.23 ; 365/185.29	Gotou, Hiroshi		<input type="checkbox"/>						
126	365/185.03 ; 365/185.19 ; 365/185.22	Korsh, George J. , et al.		<input type="checkbox"/>						
127	365/184 ; 365/189.03 ; 365/189.05	Tanaka, Tomoharu , et al.		<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
128	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5815425 A	19980929		Combined digital write and analog rewrite process for non-volatile memory	365/45
129	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5801993 A	19980901		Nonvolatile memory device	365/185.28
130	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5801980 A	19980901		Testing of an analog memory using an on-chip digital input/output	365/45
131	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5796657 A	19980818		Flash memory with flexible erasing size from multi-byte to multi-block interface	365/185.11
132	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5790453 A	19980804		Apparatus and method for reading state of multistate non-volatile memory cells	365/185.03
133	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5781478 A	19980714		Nonvolatile semiconductor memory device	365/185.11
134	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5777923 A	19980707		Flash memory read/write controller	365/185.11
135	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5776810 A	19980707		Method for forming EEPROM with split gate source side injection	438/258

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
128	365/185.03		Wong, Sau C. , et al.	<input type="checkbox"/>						
129	365/185.21 ; 365/185.29 ; 365/185.33 ; 365/218		Choi, Woong Lim	<input type="checkbox"/>						
130	365/201 ; 714/719		Wong, Sau C. , et al.	<input type="checkbox"/>						
131	365/185.29 ; 365/185.33 ; 365/189.05 ; 365/230.03 ; 365/230.06 ; 365/230.08		Lee, Peter W. , et al.	<input type="checkbox"/>						
132	365/168 ; 365/208		Chevallier, Christophe J.	<input type="checkbox"/>						
133	365/185.12 ; 365/185.17 ; 365/185.18 ; 365/185.24		Takeuchi, Ken , et al.	<input type="checkbox"/>						
134	365/185.18 ; 365/185.21 ; 365/185.33		Lee, Peter W. , et al.	<input type="checkbox"/>						
135	438/262 ; 438/264 ; 438/267		Guterman, Daniel C. , et al.	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
136	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5774397 A	19980630			Non-volatile semiconductor memory device and method of programming a non-volatile memory cell to a predetermined state	365/185.19
137	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5774395 A	19980630			Electrically erasable reference cell for accurately determining threshold voltage of a non-volatile memory at a plurality of threshold voltage levels	365/185.3
138	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5771346 A	19980623			Apparatus and method for detecting over-programming condition in multistate memory device	714/42
139	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5768287 A	19980616			Apparatus and method for programming multistate memory device	714/719
140	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5768193 A	19980616			Bit-refreshable method and circuit for refreshing a nonvolatile flash memory	365/185.25
141	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5768191 A	19980616			Methods of programming multi-state integrated circuit memory devices	365/185.22
142	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5768188 A	19980616			Multi-state non-volatile semiconductor memory and method for driving the same	365/185.03

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
136	365/185.03 ; 365/185.22	Endoh, Tetsuo , et al.		<input type="checkbox"/>						
137	365/185.03 ; 365/185.24 ; 365/210	Richart, Robert B. , et al.		<input type="checkbox"/>						
138	365/185.22	Norman, Robert D. , et al.		<input type="checkbox"/>						
139		Norman, Robert D. , et al.		<input type="checkbox"/>						
140	365/185.12 ; 365/185.33	Lee, Peter W. , et al.		<input type="checkbox"/>						
141	365/185.03 ; 365/185.12 ; 365/185.2	Choi, Young-Joon , et al.		<input type="checkbox"/>						
142	365/185.17 ; 365/189.05	Park, Jong-Wook , et al.		<input type="checkbox"/>						

U	V	1	Document ID	Issue Date	Pages	Title	Current OR
143	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5768184 A	19980616		Performance non-volatile semiconductor memory device	365/185.03
144	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5764571 A	19980609		Electrically alterable non-volatile memory with N-bits per cell	365/189.01
145	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5764568 A	19980609		Method for performing analog over-program and under-program detection for a multistate memory cell	365/185.03
146	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5761222 A	19980602		Memory device having error detection and correction function, and methods for reading, writing and erasing the memory device	714/773
147	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5757700 A	19980526		Semiconductor memory device	365/189.01
148	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5754475 A	19980519		Bit line discharge method for reading a multiple bits-per-cell flash EEPROM	365/185.25
149	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5754469 A	19980519		Page mode floating gate memory device storing multiple bits per cell	365/185.03
150	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5751635 A	19980512		Read circuits for analog memory cells	365/185.19
151	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5751634 A	19980512		Non-volatile semiconductor memory device for storing multivalue data and readout/write-in method therefor	365/185.17

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
143	365/185.2		Hayashi, Yutaka et al.	<input type="checkbox"/>						
144	365/168 ; 365/189.07 ; 365/201		Banks, Gerald J.	<input type="checkbox"/>						
145	365/185.19 ; 365/185.22 ; 365/185.24		Chevallier, Christophe J.	<input type="checkbox"/>						
146			Baldi, Livio	<input type="checkbox"/>						
147	365/230.01		Kobayashi, Yasuhiro	<input type="checkbox"/>						
148	365/185.2		Bill, Colin et al.	<input type="checkbox"/>						
149	365/185.12 ; 365/185.22		Hung, Chun-Hsiung et al.	<input type="checkbox"/>						
150	327/93 ; 327/94 ; 365/185.03 ; 365/185.2 ; 365/185.21		Wong, Sau C. et al.	<input type="checkbox"/>						
151	365/185.18 ; 365/185.2 ; 365/185.24		Itoh, Yasuo	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
152	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5748535 A	19980505		Advanced program verify for page mode flash memory	365/185.22
153	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5748534 A	19980505		Feedback loop for reading threshold voltage	365/185.21
154	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5745412 A	19980428		Programmable nonvolatile memory and method of programming the same	365/185.1
155	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5745409 A	19980428		Non-volatile memory with analog and digital interface and storage	365/185.03
156	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5724366 A	19980303		Semiconductor memory device	714/719
157	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 57117632 A	19980210		Apparatus and method for multiple-level storage in non-volatile memories	365/185.2
158	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 57115196 A	19980203		Method for driving a non-volatile semiconductor memory	365/185.23
159	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 57112180 A	19980127		EEPROM with split gate source side injection	438/263
160	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5706242 A	19980106		Semiconductor device having a controllable voltage supply	365/226
161	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5696717 A	19971209		Nonvolatile integrated circuit memory devices having adjustable	365/185.22
162	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5694358 A	19971202		erase/program threshold voltage verification capability	365/185.08
163	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5694356 A	19971202		High resolution analog storage EEPROM and flash EEPROM	365/185.03
164	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5687126 A	19971111		Semiconductor device	365/208

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
152	365/185.05 ; 365/185.11	Lin, Tien-Ler , et al.		□	□	□	□	□	□	□
153	327/54 ; 365/207	Dunlap, Frank M. , et al.		□	□	□	□	□	□	□
154	365/185.22	Choi, Woong-Lim		□	□	□	□	□	□	□
155	365/236 ; 365/45	Wong, Sau C. , et al.		□	□	□	□	□	□	□
156	365/201 365/185.01	Furutani, Kiyohiro		□	□	□	□	□	□	□
157	365/185.03 ; 365/185.24	Richard, Robert B. , et al.		□	□	□	□	□	□	□
158	365/185.08	Odake, Yoshinori , et al.		□	□	□	□	□	□	□
159	438/264 ; 438/594	Guterman, Daniel C. , et al.		□	□	□	□	□	□	□
160	365/189.09 ; 365/230.06	Hirano, Hiroshige , et al.		□	□	□	□	□	□	□
161	365/185.12 ; 365/185.17 ; 365/185.23	Koh, Yong-Nam		□	□	□	□	□	□	□
162	365/189.05 ; 365/203 ; 365/63	Kawahara, Takayuki , et al.		□	□	□	□	□	□	□
163	365/185.19 ; 365/185.21 ; 365/185.22	Wong, Sau C. , et al.		□	□	□	□	□	□	□
164	365/189.06 ; 365/207	Hirano, Hiroshige , et al.		□	□	□	□	□	□	□

	U	1	Document ID	Issue Date	Pages	Title	Current OR
165	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5687115 A	19971111		Write circuits for analog memory	365/185.03
166	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5684739 A	19971104		Apparatus and method for determining current or voltage of a semiconductor device	365/185.03
167	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5671388 A	19970923		Method and apparatus for performing write operations in multi-level cell storage device	711/103
168	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5657332 A	19970812		Soft errors handling in EEPROM devices	714/763
169	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5652719 A	19970729		Nonvolatile semiconductor memory device	365/185.03
170	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5638320 A	19970610		High resolution analog storage EEPROM and flash EEPROM	365/185.03
171	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5627779 A	19970506		Non-volatile semiconductor memory having an array of non-volatile memory cells and method for driving the same	365/185.01
172	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5621684 A	19970415		Nonvolatile semiconductor member with different pass potential applied to the first two adjacent word	365/185.17

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
165	365/185.11 ; 365/185.21 ; 365/185.22 ; 365/185.23	257/315	Wong, Sau C. , et al.	<input type="checkbox"/>						
166	257/316 ; 257/318 ; 365/185.2 ; 365/185.21		Takeuchi, Nobuyoshi	<input type="checkbox"/>						
167	365/168 ; 365/185.03 ; 711/165		Hasbun, Robert N.	<input type="checkbox"/>						
168	365/184 ; 365/189.07 ; 365/189.11 ; 714/721		Auclair, Daniel L. , et al.	<input type="checkbox"/>						
169	365/185.17 ; 365/185.22		Tanaka, Tomoharu , et al.	<input type="checkbox"/>						
170	365/185.19 ; 365/185.21		Wong, Sau C. , et al.	<input type="checkbox"/>						
171	257/316 ; 257/322 ; 365/185.02 ; 365/185.12 ; 365/185.18 ; 365/185.21		Odake, Yoshinori , et al.	<input type="checkbox"/>						
172	365/185.23 ; 365/185.24		Jung, Tae-Sung	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
173	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5602789 A		19970211		Electrically erasable and programmable non-volatile and multi-level memory system with write-verify controller	365/185.03
174	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5597244 A		19970128		Electronic typewriter with spell verify	400/63
175	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5596526 A		19970121		Non-volatile memory system of multi-level transistor cells and methods using same	365/185.17
176	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5594697 A		19970114		Semiconductor device	365/185.21
177	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5574879 A		19961112		Addressing modes for a dynamic single bit per cell to multiple bit per cell memory	711/100
178	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5570315 A		19961029		Multi-state EEPROM having write-verify control circuit	365/185.22
179	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5566125 A		19961015		Method and circuitry for storing discrete amounts of charge in a single memory element	365/45
180	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5566111 A		19961015		Method for programming a nonvolatile memory	365/185.22
181	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5555204 A		19960910		Non-volatile semiconductor memory device	365/185.22

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
173	365/185.12 ; 365/185.17 ; 365/185.19 ; 365/185.22 ; 365/189.05 ; 714/704		Endoh, Tetsuo , et al.	<input type="checkbox"/>						
174			Ueda, Hiroyuki , et al.	<input type="checkbox"/>						
175	365/104 ; 365/185.03 ; 365/185.22 ; 365/185.24		Assar, Mahmud , et al.	<input type="checkbox"/>						
176	365/185.03 ; 365/185.22 ; 365/189.09		Hirano, Hiroshige , et al.	<input type="checkbox"/>						
177	365/185.03 ; 365/185.33 ; 365/230.08		Wells, Steven E. , et al.	<input type="checkbox"/>						
178	365/185.03 ; 365/185.12 ; 365/185.17 ; 365/185.18 ; 365/185.21		Tanaka, Tomoharu , et al.	<input type="checkbox"/>						
179	365/185.03 ; 365/185.12 ; 365/185.22 ; 365/189.05		Fazio, Albert , et al.	<input type="checkbox"/>						
180	365/185.03 ; 365/185.2 ; 365/185.21 ; 365/185.24		Choi, Woong-Lim	<input type="checkbox"/>						
181	365/185.17 ; 365/185.18		Endoh, Tetsuo , et al.	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
182	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5537621 A	19960716		Integrated memory, method for managing it, and resultant information processing system	714/8
183	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5532964 A	19960702		Method and circuit for simultaneously programming and verifying the programming of selected EEPROM cells	365/189.09
184	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5532962 A	19960702		Soft errors handling in EEPROM devices	365/201
185	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5523972 A	19960604		Method and apparatus for verifying the programming of multi-level flash EEPROM memory	365/185.22
186	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5521865 A	19960528		Non-volatile semiconductor memory device for storing multi-value data	365/185.22
187	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5517187 A	19960514		Microchips and remote control devices comprising same	340/825.3
188	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5515317 A	19960507		Addressing modes for a dynamic single bit per cell to multiple bit per cell memory	711/100

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
182	711/5		Charlot, Didier , et al.	<input type="checkbox"/>						
183	365/185.18 ; 365/189.07		Cernea, Raul-Adrian , et al.	<input type="checkbox"/>						
184	365/184 ; 365/185.02 ; 365/185.09 ; 365/185.24		Auclair, Daniel L. , et al.	<input type="checkbox"/>						
185	365/185.03 ; 365/185.21 ; 365/185.3 ; 365/185.33 ; 365/189.07 ; 365/201		Rashid, Mamun , et al.	<input type="checkbox"/>						
186	365/185.03 ; 365/185.21 ; 365/205		Ohuchi, Kazunori , et al.	<input type="checkbox"/>						
187	340/825.31 ; 340/825.34 ; 340/825.56 ; 380/262 ; 380/274		Bruwer, Frederick J. , et al.	<input type="checkbox"/>						
188	365/185.03 ; 365/185.11 ; 365/185.21 ; 365/185.22 ; 365/230.08 ; 711/103		Wells, Steven E. , et al.	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
189	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5508958 A	19960416			Method and apparatus for sensing the state of floating gate memory cells by applying a variable gate voltage.	365/185.19
190	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5495442 A	19960227			Method and circuit for simultaneously programming and verifying the programming of selected EEPROM cells.	365/185.03
191	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5450363 A	19950912			Gray coding for a multilevel cell memory system	341/98
192	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5444656 A	19950822			Apparatus for fast internal reference cell trimming	365/185.2
193	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5440505 A	19950808			Method and circuitry for storing discrete amounts of charge in a single memory element	365/45
194	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5422842 A	19950606			Method and circuit for simultaneously programming and verifying the programming of selected EEPROM cells.	365/185.22
195	<input checked="" type="checkbox"/>	<input type="checkbox"/> US 5394362 A	19950228			Electrically alterable non-volatile memory with N-bits per memory cell	365/185.03

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
189	365/168	Fazio, Albert , et al.								
190	365/185.14 ; 365/185.16 ; 365/185.21 ; 365/185.22 ; 365/194	Cernea, Raul-Adrian , et al.								
191	365/184 ; 365/185.03 ; 365/185.21 ; 365/94	Christopherson, Mark , et al.								
192	365/185.03 ; 365/185.21 ; 365/185.24 ; 365/189.07 ; 365/189.09	Bauer, Mark , et al.								
193	365/185.03 ; 365/185.22 ; 365/189.01 ; 365/218 ; 365/230.01	Fazio, Albert , et al.								
194	365/185.14 ; 365/185.16 ; 365/185.21 ; 365/185.24	Cernea, Raul-Adrian , et al.								
195	365/185.19 ; 365/185.2 ; 365/185.22 ; 365/185.24 ; 365/185.28 ; 365/185.33	Banks, Gerald J.								

	U	1	Document ID	Issue Date	Pages	Title	Current OR
196	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5268668 A	19931207		Security/fire alarm system with group-addressing remote sensors	340/505
197	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5218569 A	19930608		Electrically alterable non-volatile memory with n-bits per memory cell	365/185.21
198	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5200959 A	19930406		Device and method for defect handling in semi-conductor memory	714/723
199	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5172338 A	19921215		Multi-state Eeprom read and write circuits and techniques	365/185.03
200	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5163039 A	19921110		Three-dimensional optical memory system	369/100
201	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5163021 A	19921110		Multi-state EEprom read and write circuits and techniques	365/185.03
202	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4872106 A	19891003		Industrial process control system with back-up data processors to take over from failed primary data processors	714/13
203	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4715002 A	19871222		System for recording a variable value, notably in a well, and for compressing stored measurement interval data	702/11

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
196	340/518 ; 340/825.07		Berube, James E.	<input type="checkbox"/>						
	365/185.19 ; 365/185.22			<input type="checkbox"/>						
197	; 365/185.29 ; 365/186 ; 365/45		Banks, Gerald J.	<input type="checkbox"/>						
198	714/710 ; 714/8		Gross, Stephen , et al.	<input type="checkbox"/>						
	365/184 ; 365/185.33		Mehrotra, Sanjay	<input type="checkbox"/>						
199	; 365/189.07 ; 365/195 ; 365/201		, et al.	<input type="checkbox"/>						
200			Lindmayer, Joseph	<input type="checkbox"/>						
	330/2 ; 365/104			<input type="checkbox"/>						
201	; 365/168 ; 365/185.22		Mehrotra, Sanjay	<input type="checkbox"/>						
	; 365/189.09 ; 365/201		, et al.	<input type="checkbox"/>						
202			Slater, Billy R.	<input type="checkbox"/>						
				<input type="checkbox"/>						
203	700/73 ; 73/152.53		Vernon, Patrick , et al.	<input type="checkbox"/>						

	U	1	Document ID	Issue Date	Pages	Title	Current OR
204	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4328542 A	19820504		Secure implementation of transition machine computer	711/163
205	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 4053752 A	19771011		Error recovery and control in a mass storage system	714/710

	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3	4	5
204	711/148		Anastas, Mark S. , et al.	<input type="checkbox"/>						
205			DeJohn, Patrick Fred , et al.	<input type="checkbox"/>						